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(REV. 2-82) Patent and Trademark OfficeAtty. Docket No.
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2826**U.S. PATENT DOCUMENTS**

*Exam Init	Document No.	Date	Name	Class	Subclass	Filing Date if Appropriate
MLT	5 1 9 8 3 7 1	03-30-93	Li	437	11	
MLT	5 6 3 3 1 7 4	05-27-97	Li	438	475	
MLT	5 0 3 4 3 4 3	07-23-91	Rouse et al.	437	86	
MLT	5 3 7 4 5 6 4	12-20-94	Bruel	437	24	
MLT	5 4 6 1 2 4 5	10-24-95	Gribnikov et al.	257	197	
MLT	6 1 4 4 0 7 2	11-7-00	Iwamatsu et al.	257	347	1-15-99

FOREIGN PATENT DOCUMENT

Document No.	Date	Country	Class	SubClass	Translator Yes No

OTHER DOCUMENTS (including Author, Title Date, Pertinent Pages, Etc.)

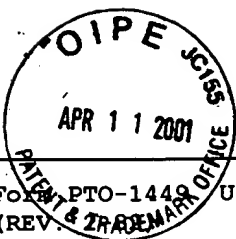
MLT	Jianming Li et al., Properties of Silicon-on-Defect-Layer Material, in: Materials Research Society Symposium Proceedings Vol. 396, David B. Paker et al., Ed., pp.745-750
MLT	Jianming Li, New annealing processes and explanation for novel silicon pn junctions formed by proton implantation, Electronics Letters, Vol. 35 (1997), pp. 133-134

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* Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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09/800,213**INFORMATION DISCLOSURE STATEMENT
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MLT			Jianming Li et al., Properties of proton-implanted p-type Si: supports for the model explaining a novel p-n junction in Si, Nuclear Instruments and Methods in Physics Research B 160 (2000), pp. 190-193
-----	--	--	---

MLT			J. S. Williams et al., The role of oxygen on the stability of gettering of metals to cavities in silicon, Applied Physics Letters, Vol. 75, No. 16, 18 October 1999, pp. 2424-2426
-----	--	--	--

MLT			K. Henttinen et al., Mechanically induced Si layer transfer in hydrogen-implanted Si wafers, Applied Physics Letters, Vol. 76, No. 17, 24 April 2000, pp. 2370-2372
-----	--	--	---

MLT			J. Grisolia et al., A transmission electron microscopy quantitative study of the growth kinetics of H platelets in Si, Applied Physics Letters, Vol. 76, No. 7, 14 February 2000, pp. 852-854
-----	--	--	---

MLT			Jianming Li, The new exploration for proton-implanted silicon: the conversion of a surface-region-purification-induced p-n junction into a p-i-n electrical structure approaching silicon on insulator, Semiconductor Sci. Technol. 15 (2000), pp. L6-L9
-----	--	--	--

MLT			J. H. Evans et al., The Annealing of Helium-induced Cavities in Silicon and the Inhibiting Role of Oxygen, Nuclear Instruments and Methods in Physics Research B28 (1987), pp. 360-363
-----	--	--	--

MLT			M. J. Goeckner et al., Plasma doping for shallow junctions, J. Vac. Sci. Technol. B 17(5), Sep/Oct 1999, pp. 2290-2293
-----	--	--	--

MLT			Dixon Tat-Kun Kwok et al., Particle-in-cell and Monte Carlo simulation of the hydrogen plasma immersion ion implantation process, Journal of Applied Physics, Vol. 86, No. 4, 15 August 1999, pp. 1817-1821
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